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WPI Acc No: 1996-121717/ 199613

XRAM Acc No: C96-038230

XRPX Acc No: N96-102156

Plasma etching with improved stability - using fluorine@ gp.  
gas to remove surface oxide film

Patent Assignee: SONY CORP (SONY )

Number of Countries: 001 Number of Patents: 002

Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week
JP 8017804	A	19960119	JP 94152475	A	19940704	199613 B
JP 3297963	B2	20020702	JP 94152475	A	19940704	200246

Priority Applications (No Type Date): JP 94152475 A 19940704

Patent Details:

Patent No Kind Lan Pg Main IPC Filing Notes

JP 8017804 A 7 H01L-021/3065

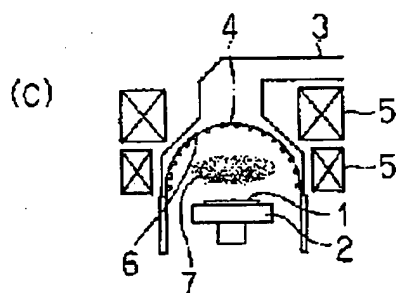
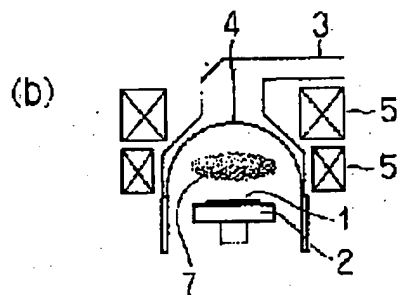
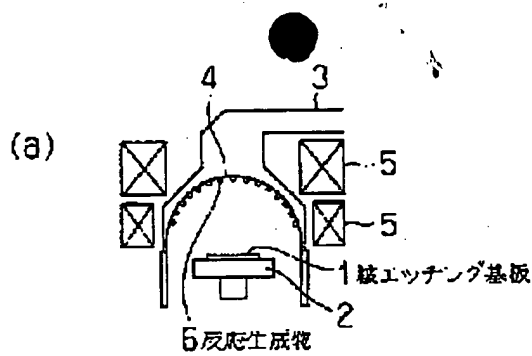
JP 3297963 B2 7 H01L-021/3065 Previous Publ. patent JP 8017804

Abstract (Basic): JP 8017804 A

Plasma discharge pretreatment with fluorine gp. gas is achieved for  
each substrate or plasma discharge post-treatment by fluorine gp. gas  
is achieved using single electrode static chuck.

ADVANTAGE -The process has improved stability and uniformity.

Dwg.1/3



Title Terms: PLASMA; ETCH; IMPROVE; STABILISED; FLUORINE; GROUP; GAS;  
 REMOVE; SURFACE; OXIDE; FILM  
 Derwent Class: L03; M14; U11  
 International Patent Class (Main): H01L-021/3065  
 International Patent Class (Additional): C23F-004/00  
 File Segment: CPI; EPI  
 Manual Codes (CPI/A-N): L04-C07D; M14-A04  
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